

NOTE BOOK PC APPLICATIONS
PORTABLE EQUIPMENTS APPLICATIONS

UNIT:mm

- Low Drain - Source ON Resistance : $R_{DS(ON)} = 26m$ (Typ.)
- High Forward Transfer Admittance : $|Y_{fs}| = S$ (Typ.)
- Low Leakage Current : $I_{DSS} = -10\mu A$ (Max.) ($V_{DS} = -30V$)
- Enhancement - Mode : $V_{th} = -0.8 \sim -2.0V$ ($V_{DS} = -10V, I_D = -1mA$)

MAXIMUM RATINGS (Ta=25)

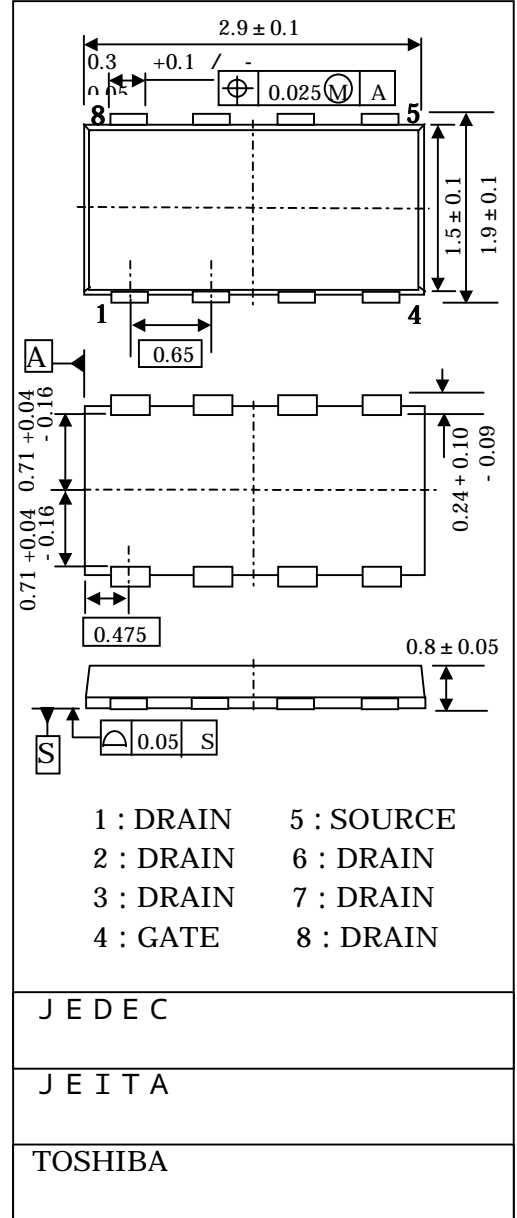
CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain - Source Voltage	V_{DSS}	-30	V
Drain - Gate Voltage ($R_{GS} = 20k$)	V_{DGR}	-30	V
Gate - Source Voltage	V_{GSS}	± 20	V
Drain Current	DC (Note1)	I_D	-6 A
	Pulse (Note1)	I_{DP}	-24 A
Drain Power Dissipation (t=5s) (Note2a)	P_D	2.5	W
Drain Power Dissipation (t=5s) (Note2b)	P_D	0.7	W
Single Pulse Avalanche Energy(Note3)	E_{AS}	5.9	mJ
Avalanche Current	I_{AR}	3	A
Repetitive Avalanche Energy (Note4)	E_{AR}	0.25	mJ
Channel Temperature	T_{ch}	150	
Storage Temperature Range	T_{stg}	-55 ~ 150	

THERMAL CHARACTERISTICS

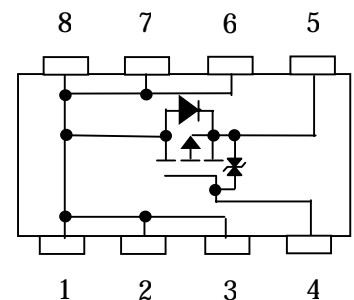
CHARACTERISTICS	SYMBOL	MAX.	UNIT
Thermal Resistance, Channel to Ambient (t=5s) (Note2a)	$R_{th(ch-a)}$	50.0	/W
Thermal Resistance, Channel to Ambient (t=5s) (Note2b)	$R_{th(ch-a)}$	178.6	/W

Note1, Note2, Note3, Note4, Note5 Please see next page.

THIS TRANSISTOR IS AN ELECTROSTATIC SENSITIVE DEVICE.
PLEASE HANDLE WITH CAUTION.



Circuit Configuration



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